

Supplementary Materials

Tailoring microstructure engineering to decouple electron-phonon transport in Se-based thermoelectric alloys

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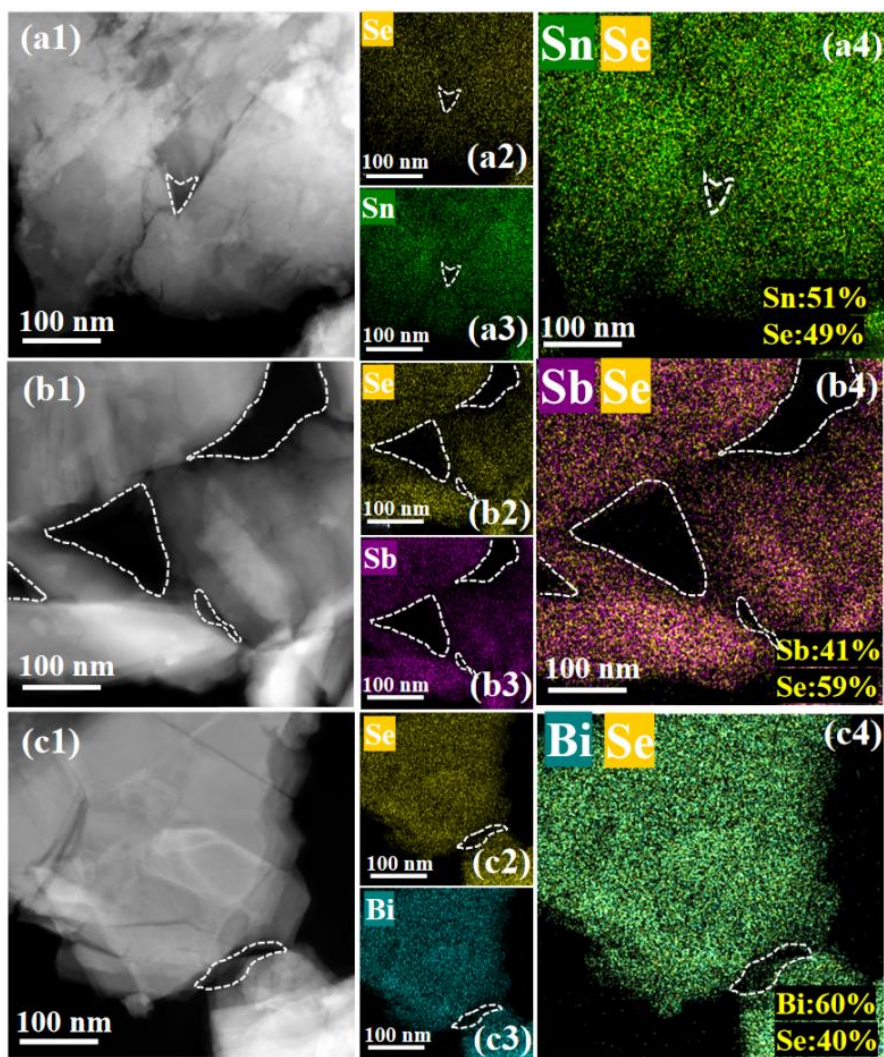


Fig. S1. (a1-c1) High-angle annular dark-field scanning transmission electron microscopy (HAADF-STEM) images, (a2-c2) the corresponding Se elemental distributions of the different materials, (a3-c3) the corresponding Sn, Sb, and Bi elemental distributions of the different materials, (a4-c4) the corresponding EDX elemental mapping results for Sn-Se, Sb-Se, and Bi-Se, respectively.

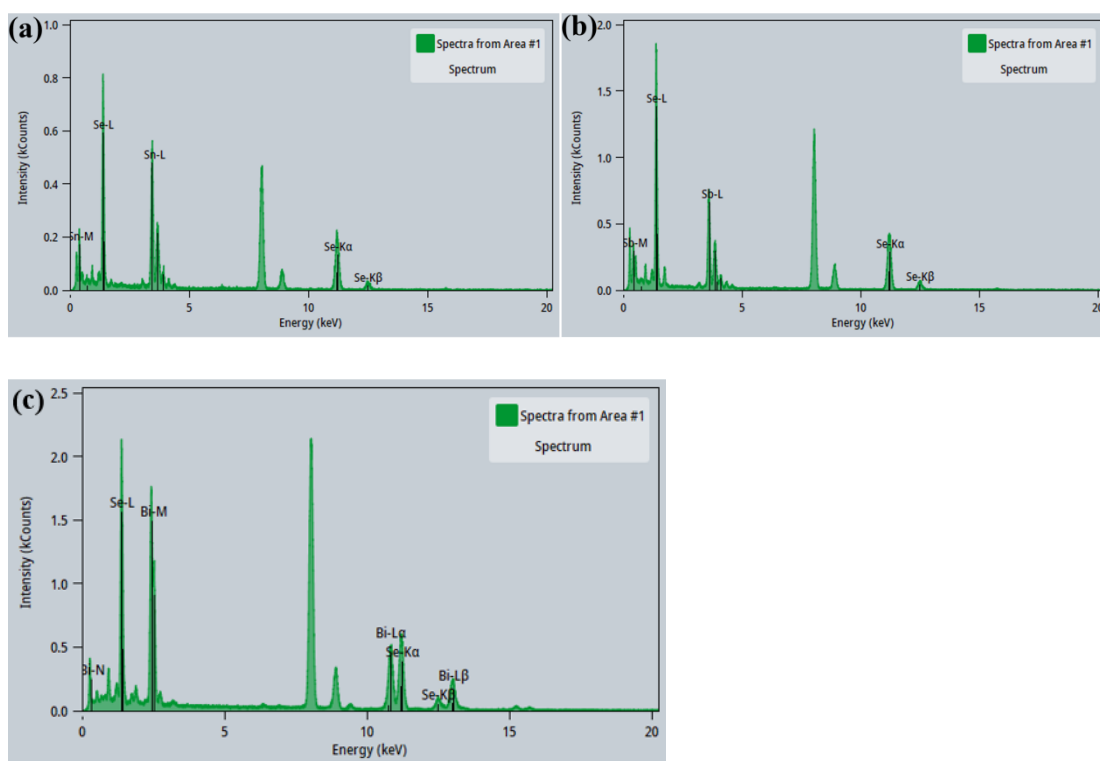


Fig. S2. (a), (b), and (c) show the EDS spectra collected from specific micro-regions of the Sn-Se, Sb-Se, and Bi-Se samples under a transmission electron microscope (TEM).

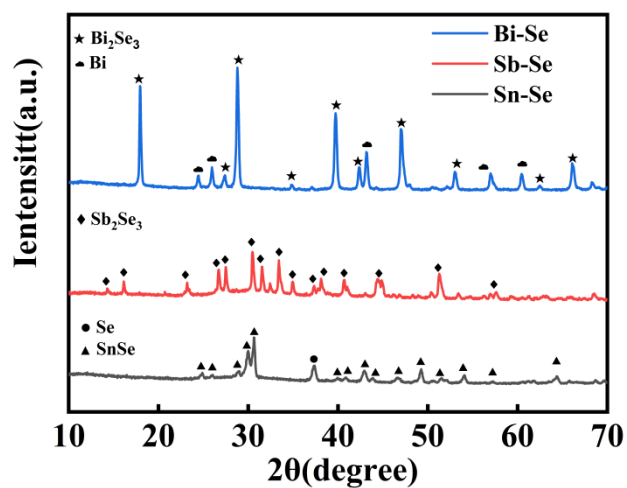


Fig. S3. XRD patterns of the Sn-Se, Sb-Se, and Bi-Se samples.